



DS55451/2/3/4, DS75450/1/2/3/4 Series Dual Peripheral Drivers

General Description

The DS75450 series of dual peripheral drivers is a family of versatile devices designed for use in systems that use TTL logic. Typical applications include high speed logic buffers, power drivers, relay drivers, lamp drivers, MOS drivers, bus drivers and memory drivers.

The DS75450 is a general purpose device featuring two standard Series 54/74 TTL gates and two uncommitted, high current, high voltage NPN transistors. The device offers the system designer the flexibility of tailoring the circuit to the application.

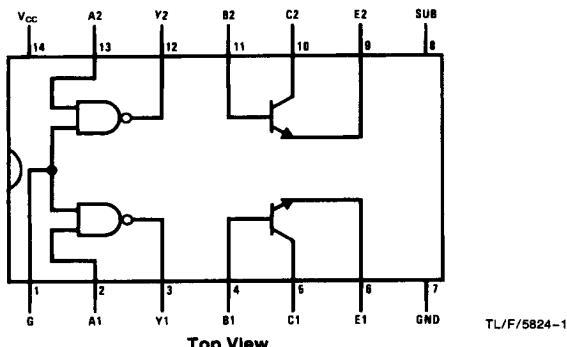
The DS55451/DS75451, DS55452/DS75452, DS55453/DS75453 and DS55454/DS75454 are dual peripheral AND, NAND, OR and NOR drivers, respectively, (positive logic)

with the output of the logic gates internally connected to the bases of the NPN output transistors.

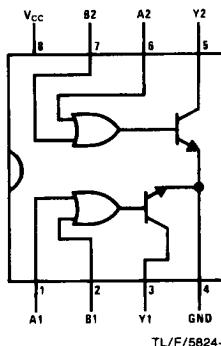
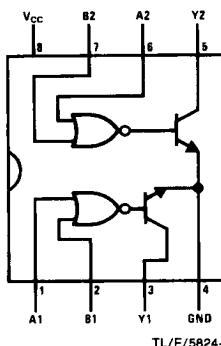
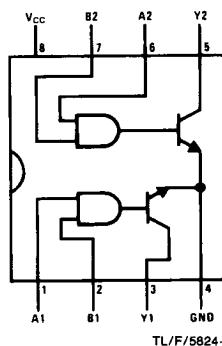
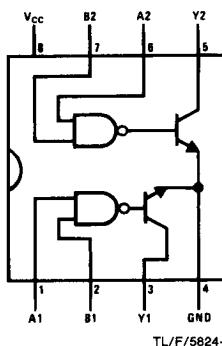
Features

- 300 mA output current capability
- High voltage outputs
- No output latch-up at 20V
- High speed switching
- Choice of logic function
- TTL compatible diode-clamped inputs
- Standard supply voltages
- Replaces TI "A" and "B" series

Connection Diagrams (Dual-In-Line and Metal Can Packages)



Top View
Order Number DS75450N
See NS Package Number N14A



Top View
Order Number DS55451J-8, Order Number DS55452J-8, Order Number DS55453J-8,
DS75451M or DS75451N DS75452M or DS75452N DS75453M or DS75453N
See NS Package Numbers J08A, M08A* or N08E

*See Note 6 and Appendix E regarding S.O. package power dissipation constraints.

Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage, (V_{CC}) (Note 2)	7.0V	DS75450 Maximum Power (Note 6)
Input Voltage	5.5V	Dissipation* at 25°C Cavity Package Molded Package
Inter-Emitter Voltage (Note 3)	5.5V	1308 mW 1207 mW
V_{CC} -to-Substrate Voltage DS75450	35V	DS75451/2/3/4 Maximum Power (Note 6)
Collector-to-Substrate Voltage DS75450	35V	Dissipation† at 25°C Cavity Package Molded DIP Package TO-5 Package SO Package
Collector-Base Voltage DS75450	35V	1090 mW 957 mW 760 mW 632 mW
Collector-Emitter Voltage (Note 4) DS75450	30V	Storage Temperature Range Lead Temperature (Soldering, 4 sec.)
Emitter-Base Voltage DS75450	5.0V	−65°C to +150°C 260°C
Output Voltage (Note 5) DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454	30V	Temperature, (T_A) DS5545X DS7545X
Collector Current (Note 6) DS75450	300 mA	−55 °C +125 °C 0 °C +70 °C
Output Current (Note 6) DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454	300 mA	*Derate cavity package 8.7 mW/°C above 25°C; derate molded package 9.7 mW/°C above 25°C. †Derate cavity package 7.3 mW/°C above 25°C; derate molded package 7.7 mW/°C above 25°C; derate TO-5 package 5.1 mW/°C above 25°C; derate SO package 7.56 mW/°C above 25°C.

Operating Conditions (Note 7)

Min	Max	Units
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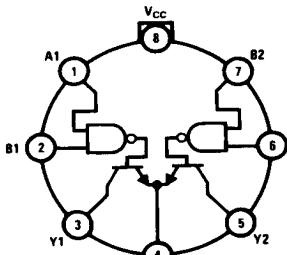
Supply Voltage, (V_{CC})	4.5	5.5	V
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DS5545X	4.75	5.25	V
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Temperature, (T_A)	−55	+125	°C
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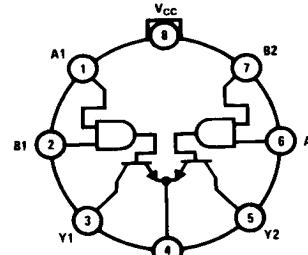
DS5545X	0	+70	°C
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Connection Diagrams (Dual-In-Line and Metal Can Packages) (Continued)



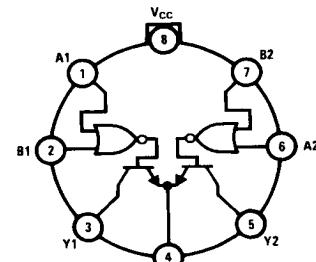
Top View

TL/F/5824-6



Top View

TL/F/5824-7



Top View

TL/F/5824-8

Order Number DS55451H

Order Number DS55452H

Order Number DS55453H
See NS Package Number H08C

Electrical Characteristics DS75450 (Notes 8 and 9)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
TTL GATES						
V_{IH}	High Level Input Voltage	(Figure 1)		2		V
V_{IL}	Low Level Input Voltage	(Figure 2)			0.8	V
V_I	Input Clamp Voltage	$V_{CC} = \text{Min}$, $I_I = -12 \text{ mA}$, (Figure 3)			-1.5	V
V_{OH}	High Level Output Voltage	$V_{CC} = \text{Min}$, $V_{IL} = 0.8 \text{ V}$, $I_{OH} = -400 \mu\text{A}$, (Figure 2)	2.4	3.3		V
V_{OL}	Low Level Output Voltage	$V_{CC} = \text{Min}$, $V_{IH} = 2 \text{ V}$, $I_{OL} = 16 \text{ mA}$ (Figure 1)		0.22	0.4	V
I_I	Input Current at Maximum Input Voltage	$V_{CC} = \text{Max}$, $V_I = 5.5 \text{ V}$, (Figure 4)	Input A		1	mA
			Input G		2	mA

Electrical Characteristics DS75450 (Notes 8 and 9) (Continued)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
TTL GATES (Continued)						
I _{IH}	High Level Input Current	V _{CC} = Max, V _I = 2.4V, (Figure 4)	Input A		40	μA
			Input G		80	μA
I _{IL}	Low Level Input Current	V _{CC} = Max, V _I = 0.4V, (Figure 3)	Input A		-1.6	mA
			Input G		-3.2	mA
I _{OS}	Short Circuit Output Current	V _{CC} = Max, (Figure 5), (Note 10)		-18	-55	mA
I _{ICCH}	Supply Current	V _{CC} = Max, V _I = 0V, Outputs High, (Figure 6)		2	4	mA
I _{ICCL}	Supply Current	V _{CC} = Max, V _I = 5V, Outputs Low, (Figure 6)		6	11	mA

OUTPUT TRANSISTORS

V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0 μA	35			V
V _{(BR)CER}	Collector-Emitter Breakdown Voltage	I _C = 100 μA, R _{BE} = 500Ω	30			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0 μA	5			V
h _{FE}	Static Forward Current Transfer Ratio	V _{CE} = 3V, (Note 11)	T _A = +25°C	I _C = 100 mA	25	
				I _C = 300 mA	30	
			T _A = 0°C	I _C = 100 mA	20	
				I _C = 300 mA	25	
V _{BE}	Base-Emitter Voltage	(Note 11)	I _B = 10 mA, I _C = 100 mA	0.85	1	V
			I _B = 30 mA, I _C = 300 mA	1.05	1.2	V
V _{CESAT}	Collector-Emitter Saturation Voltage	(Note 11)	I _B = 10 mA, I _C = 100 mA	0.25	0.4	V
			I _B = 30 mA, I _C = 300 mA	0.5	0.7	V

Electrical Characteristics (Continued)

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 (Notes 8 and 9)

Symbol	Parameter	Conditions	Min	Typ	Max	Units		
V _{IH}	High-Level Input Voltage	(Figure 7)	2			V		
					0.8	V		
V _{IL}	Low-Level Input Voltage							
V _I	Input Clamp Voltage	V _{CC} = Min, I _I = -12 mA			-1.5	V		
I _{OL}	Low-Level Output Voltage	V _{CC} = Min, (Figure 7)	V _{IL} = 0.8V	I _{OL} = 100 mA	DS55451, DS55453	0.25	0.5	V
					DS75451, DS75453	0.25	0.4	V
				I _{OL} = 300 mA	DS55451, DS55453	0.5	0.8	V
					DS75451, DS75453	0.5	0.7	V
			V _{IH} = 2V	I _{OL} = 100 mA	DS55452, DS55454	0.25	0.5	V
					DS75452, DS75454	0.25	0.4	V
				I _{OL} = 300 mA	DS55452, DS55454	0.5	0.8	V
					DS75452, DS75454	0.5	0.7	V
I _{OH}	High-Level Output Current	V _{CC} = Min, (Figure 7)	V _{OH} = 30V	V _{IH} = 2V	DS55451, DS55453		300	μA
					DS75451, DS75453		100	μA
			V _{IL} = 0.8V	V _{IH} = 2V	DS55452, DS55454		300	μA
					DS75452, DS75454		100	μA
I _I	Input Current at Maximum Input Voltage	V _{CC} = Max, V _I = 5.5V, (Figure 9)				1		mA

Electrical Characteristics (Continued)

DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 (Notes 8 and 9) (Continued)

Symbol	Parameter	Conditions			Min	Typ	Max	Units
I_{IH}	High-Level Input Current	$V_{CC} = \text{Max}$, $V_I = 2.4V$, (Figure 9)					40	μA
I_{IL}	Low-Level Input Current	$V_{CC} = \text{Max}$, $V_I = 0.4V$, (Figure 8)			-1	-1.6		mA
I_{CCH}	Supply Current, Outputs High	$V_{CC} = \text{Max}$, (Figure 10)	$V_I = 5V$	DS55451/DS75451	7	11		mA
			$V_I = 0V$	DS55452/DS75452	11	14		mA
			$V_I = 5V$	DS55453/DS75453	8	11		mA
			$V_I = 0V$	DS55454/DS75454	13	17		mA
I_{CCL}	Supply Current, Outputs Low	$V_{CC} = \text{Max}$, (Figure 10)	$V_I = 0V$	DS55451/DS75451	52	65		mA
			$V_I = 5V$	DS55452/DS75452	56	71		mA
			$V_I = 0V$	DS55453/DS75453	54	68		mA
			$V_I = 5V$	DS55454/DS75454	61	79		mA

Switching Characteristics DS75450 ($V_{CC} = 5V$, $T_A = 25^\circ C$)

Symbol	Parameter	Conditions			Min	Typ	Max	Units
t_{PLH}	Propagation Delay Time, Low-to-High Level Output	$C_L = 15 pF$	$R_L = 400\Omega$, TTL Gates, (Figure 12)			12	22	ns
			$R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)			20	30	ns
t_{PHL}	Propagation Delay Time, High-to-Low Level Output	$C_L = 15 pF$	$R_L = 400\Omega$, TTL Gates, (Figure 12)			8	15	ns
			$R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)			20	30	ns
t_{TLH}	Transition Time, Low-to-High Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)				7	12	ns
t_{THL}	Transition Time, High-to-Low Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_C \approx 200 \text{ mA}$, Gates and Transistors Combined, (Figure 14)				9	15	ns
V_{OH}	High-Level Output Voltage after Switching	$V_S = 20V$, $I_C \approx 300 \text{ mA}$, $R_{BE} = 500\Omega$, (Figure 15)		$V_S - 6.5$				mV
t_D	Delay Time	$I_C = 200 \text{ mA}$, $I_{B(1)} = 20 \text{ mA}$, $I_B = -40 \text{ mA}$, $V_{BE(OFF)} = -1V$, $C_L = 15 pF$, $R_L = 50\Omega$, (Figure 13), (Note 12)			8	15		ns
t_R	Rise Time				12	20		ns
t_S	Storage Time				7	15		ns
t_F	Full Time				6	15		ns

Switching Characteristics (Continued)DS55451/DS75451, DS55452/DS75452, DS55453/DS75453, DS55454/DS75454 ($V_{CC} = 5V$, $T_A = 25^\circ C$)

Symbol	Parameter	Conditions			Min	Typ	Max	Units
t_{PLH}	Propagation Delay Time, Low-to-High Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)	$DS55451/DS75451$		18	25		ns
			$DS55452/DS75452$		26	35		ns
			$DS55453/DS75453$		18	25		ns
			$DS55454/DS75454$		27	35		ns
t_{PHL}	Propagation Delay Time, High-to-Low Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)	$DS55451/DS75451$		18	25		ns
			$DS55452/DS75452$		24	35		ns
			$DS55453/DS75453$		16	25		ns
			$DS55454/DS75454$		24	35		ns
t_{TLH}	Transition Time, Low-to-High Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)			5	8		ns
t_{THL}	Transition Time, High-to-Low Level Output	$C_L = 15 pF$, $R_L = 50\Omega$, $I_O \approx 200 \text{ mA}$, (Figure 14)			7	12		ns
V_{OH}	High-Level Output Voltage after Switching	$V_S = 20V$, $I_O \approx 300 \text{ mA}$, (Figure 15)		$V_S - 6.5$				mV

Switching Characteristics (Continued)

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Temperature Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Voltage values are with respect to network ground terminal unless otherwise specified.

Note 3: The voltage between two emitters of a multiple-emitter transistor.

Note 4: Value applies when the base-emitter resistance (R_{BE}) is equal to or less than 500Ω .

Note 5: The maximum voltage which should be applied to any output when it is in the "OFF" state.

Note 6: Both halves of these dual circuits may conduct rated current simultaneously; however, power dissipation averaged over a short time interval must fall within the continuous dissipation rating.

Note 7: For the DS75450 only, the substrate (pin 8) must always be at the most-negative device voltage for proper operation.

Note 8: Unless otherwise specified min/max limits apply across the -55°C to $+125^\circ\text{C}$ temperature range for the DS55450 series and across the 0°C to $+70^\circ\text{C}$ range for the DS75450 series. All typicals are given for $V_{CC} = +5\text{V}$ and $T_A = 25^\circ\text{C}$.

Note 9: All currents into device pins shown as positive, out of device pins as negative, all voltages referenced to ground unless otherwise noted. All values shown as max or min on absolute value basis.

Note 10: Only one output at a time should be shorted.

Note 11: These parameters must be measured using pulse techniques. $t_W = 300\ \mu\text{s}$, duty cycle $< 2\%$.

Note 12: Applies to output transistors only.

Truth Tables (H = high level, L = low level)

DS55451/DS75451

A	B	Y
L	L	L (ON State)
L	H	L (ON State)
H	L	L (ON State)
H	H	H (OFF State)

DS55453/DS75453

A	B	Y
L	L	L (ON State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	H (OFF State)

DS55452/DS75452

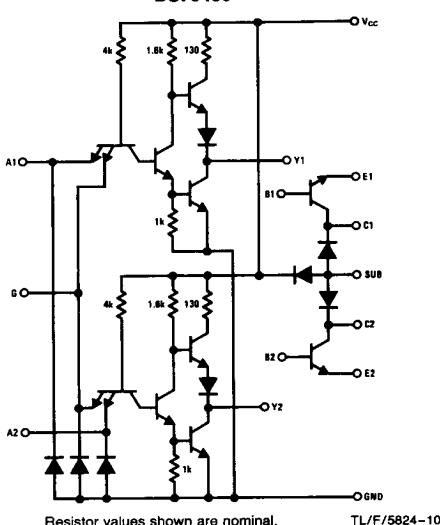
A	B	Y
L	L	H (OFF State)
L	H	H (OFF State)
H	L	H (OFF State)
H	H	L (ON State)

DS55454/DS75454

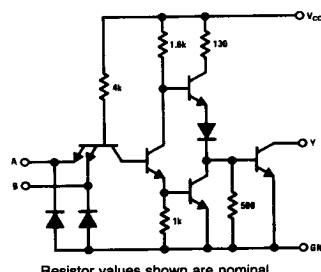
A	B	Y
L	L	H (OFF State)
L	H	L (ON State)
H	L	L (ON State)
H	H	L (ON State)

Schematic Diagrams

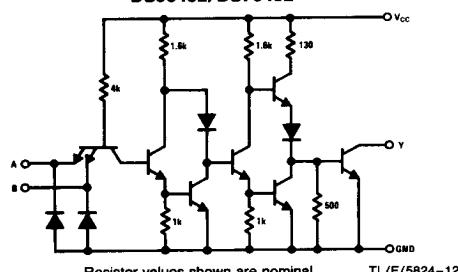
DS75450



DS55451/DS75451

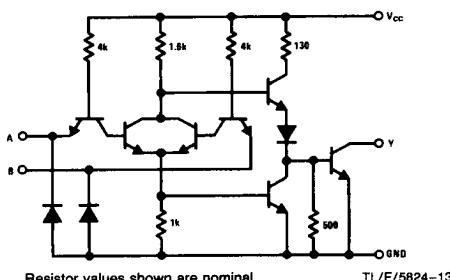


DS55452/DS75452

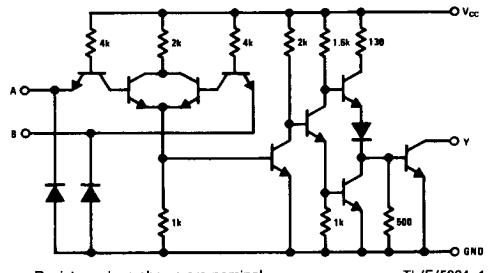


Schematic Diagrams (Continued)

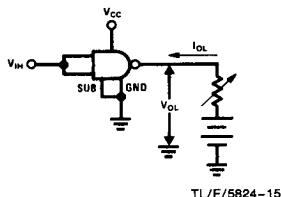
DS55453/DS75453



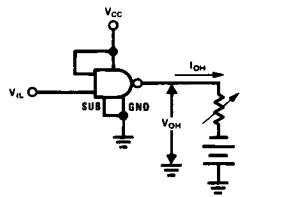
DS55454/DS75454



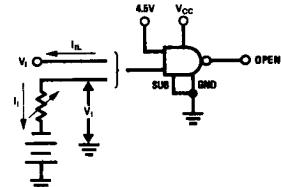
DC Test Circuits



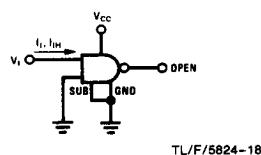
Both inputs are tested simultaneously.

FIGURE 1. V_{IH} , V_{OL} 

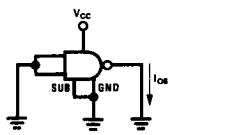
Each input is tested separately.

FIGURE 2. V_{IL} , V_{OH} 

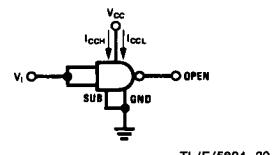
Each input is tested separately.

FIGURE 3. V_{IL} , I_{IL} 

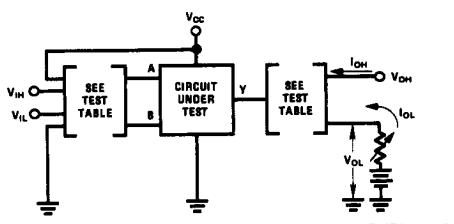
Each input is tested separately.

FIGURE 4. I_L , I_{IH} 

Each input is tested separately.

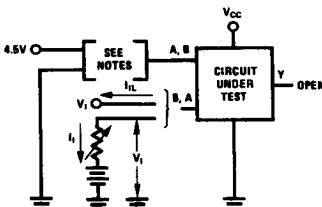
FIGURE 5. I_{OS} 

Both gates are tested simultaneously.

FIGURE 6. I_{CCH} , I_{CCL} FIGURE 7. V_{IH} , V_{IL} , I_{OH} , V_{OL}

Circuit	Input Under Test	Other Input	Output	
			Apply	Measure
DS55451	V_{IH}	V_{IH}	V_{OH}	I_{OH}
	V_{IL}	V_{CC}	I_{OL}	V_{OL}
DS55452	V_{IH}	V_{IH}	I_{OL}	V_{OL}
	V_{IL}	V_{CC}	V_{OH}	I_{OH}
DS55453	V_{IH}	Gnd	V_{OH}	I_{OH}
	V_{IL}	V_{IL}	I_{OL}	V_{OH}
DS55454	V_{IH}	Gnd	I_{OL}	V_{OL}
	V_{IL}	V_{IL}	V_{OH}	I_{OH}

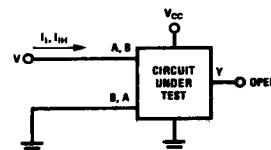
DC Test Circuits (Continued)



Note A: Each input is tested separately.
Note B: When testing DS55453/DS75453,
DS55454/DS75454, input not
under test is grounded.
For all other circuits it is at 4.5V.

TI / F / 5824-22

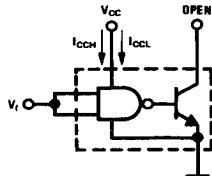
FIGURE 8. V_L , V_{IL}



Each input is tested separately

TL/F/5824-23

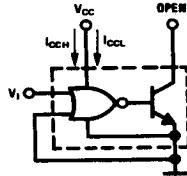
FIGURE 9. I_1 , I_{KH}



Both gates are tested simultaneously.

TL/F/5824-24

FIGURE 10. ICCH, ICCI for AND, NAND Circuits

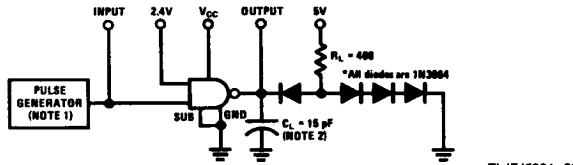


Both gates are tested simultaneously.

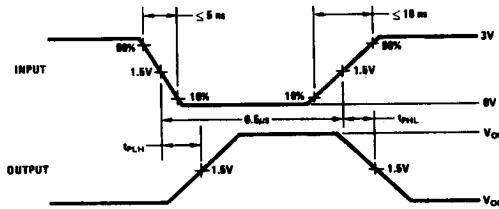
TL/F/5824-25

FIGURE 11. I_{ccH} , I_{ccL} for OR, NOR Circuits

AC Test Circuits and Switching Time Waveforms



TL/F/5824-21



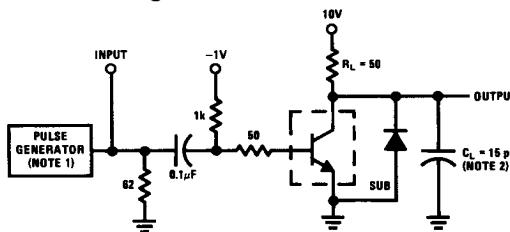
TL/F/5824-27

Note 1: The pulse generator has the following characteristics: PRR = 1 MHz, $Z_{\text{OUT}} \approx 50\Omega$.

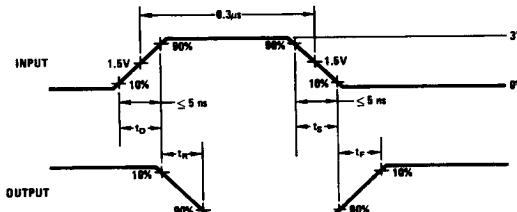
Note 2: C_1 includes probe and jig capacitance.

FIGURE 12. Propagation Delay Times, Each Gate (DS75450 Only)

AC Test Circuits and Switching Time Waveforms (Continued)



TL/F/5824-28

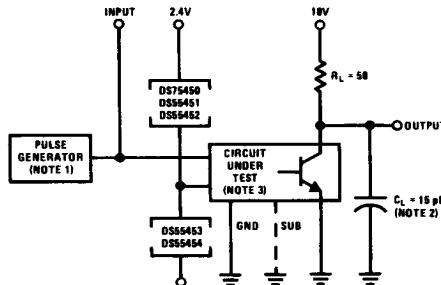


TL/F/5824-29

Note 1: The pulse generator has the following characteristics: duty cycle $\leq 1\%$, $Z_{OUT} \approx 50\Omega$.

Note 2: C_L includes probe and jig capacitance.

FIGURE 13. Switching Times, Each Transistor (DS75450 Only)

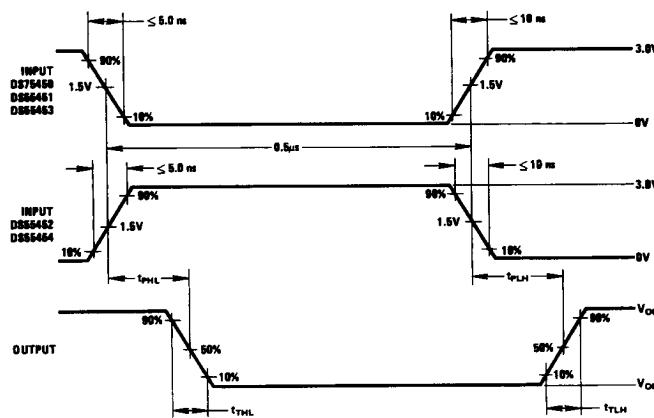


TL/F/5824-30

Note 1: The pulse generator has the following characteristics: PRR = 1.0 MHz, $Z_{OUT} \approx 50\Omega$.

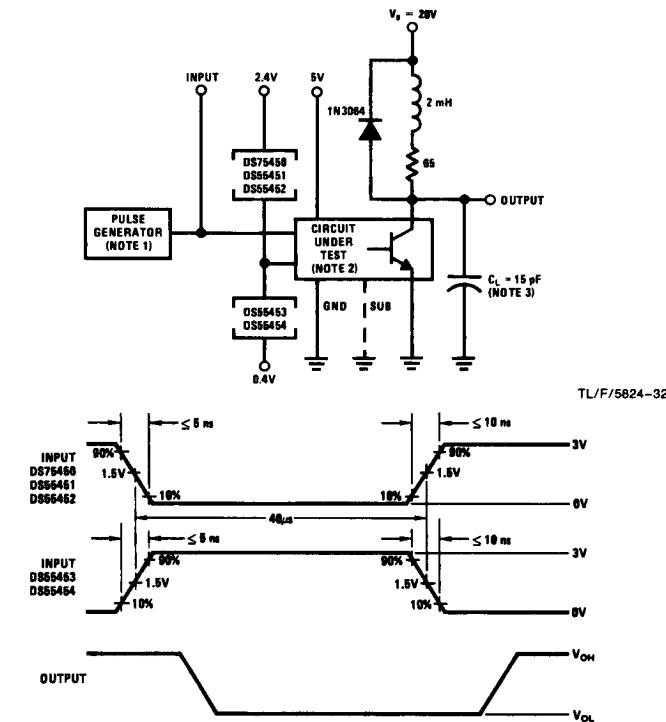
Note 2: C_L includes probe and jig capacitance.

Note 3: When testing DS75450, connect output V to transistor base and ground the substrate terminal.



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FIGURE 14. Switching Times of Complete Drivers

AC Test Circuits and Switching Time Waveforms (Continued)

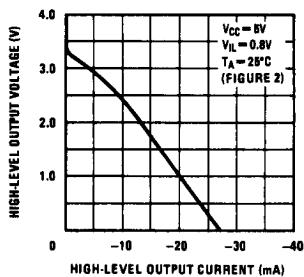
Note 1: The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_{OUT} \approx 50\Omega$.

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Note 2: When testing DS75450, connect output V to transistor base with a 600Ω resistor from there to ground and ground the substrate terminal.

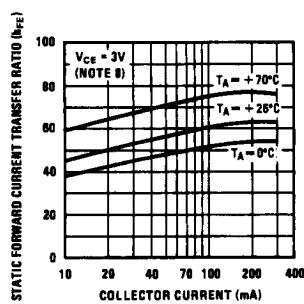
Note 3: C_L includes probe and jig capacitance.

FIGURE 15. Latch-UP Test of Complete Drivers

Typical Performance Characteristics

TL/F/5824-34

FIGURE 16. DS75450 TTL Gate High-Level Output Voltage vs High-Level Output Current



TL/F/5824-35

FIGURE 17. DS75450 Transistor Static Forward Current Transfer Ratio vs Collector Current

Typical Performance Characteristics (Continued)

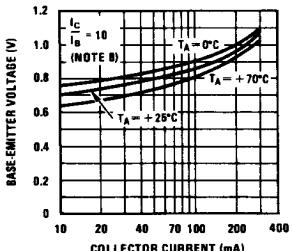


FIGURE 18. DS75450 Transistor Base-Emitter Voltage vs Collector Current

TL/F/5824-36

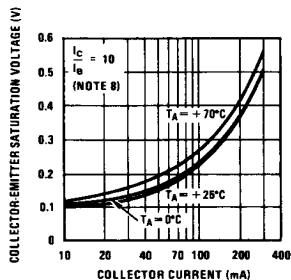


FIGURE 19. Transistor Collector-Emitter Saturation Voltage vs Collector Current

TL/F/5824-37

Typical Applications

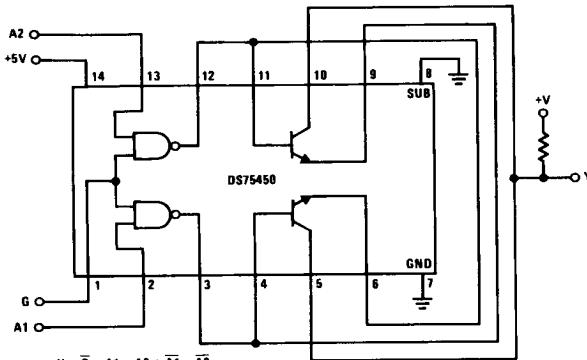


FIGURE 20- Gated Comparator

TL/F/5824-38

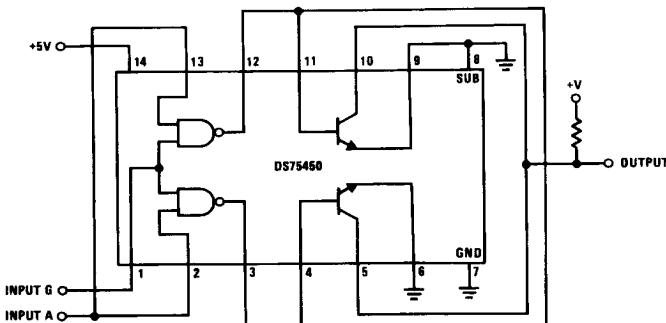
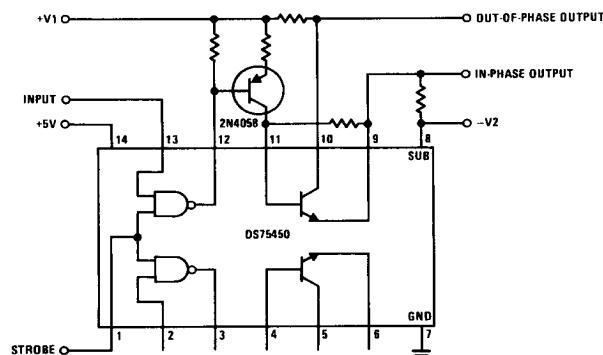
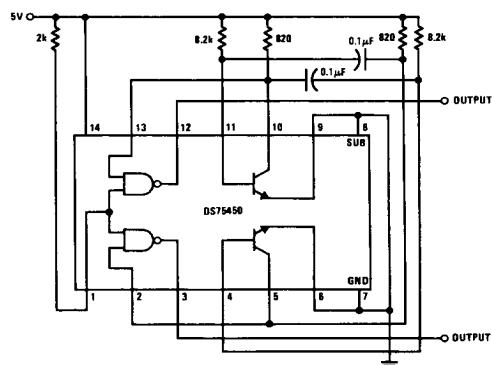


FIGURE 21. 500 mA Sink

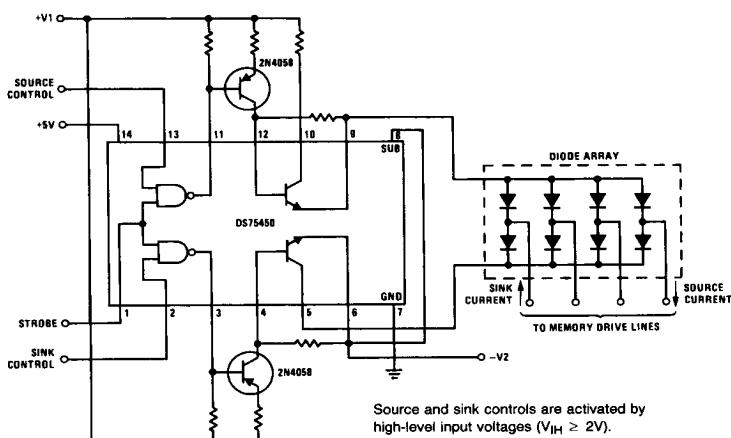
TI/E/5824-39

Typical Applications (Continued)

TL/F/5824-40

FIGURE 22. Floating Switch

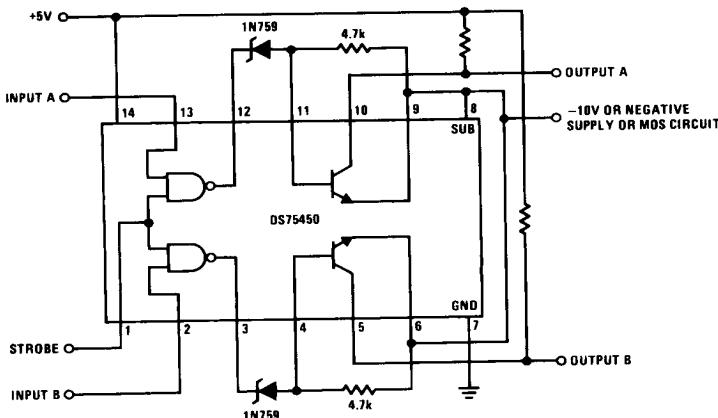
TL/F/5824-41

FIGURE 23. Square-Wave Generator

TL/F/5824-42

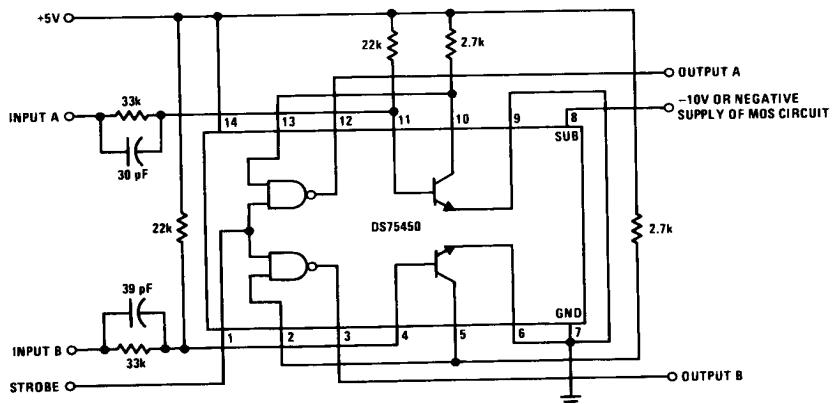
FIGURE 24. Core Memory Driver

Typical Applications (Continued)



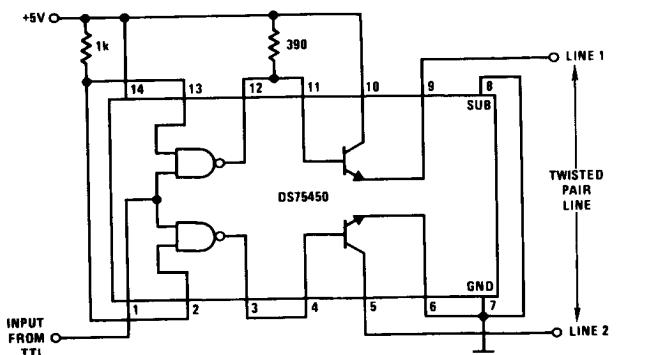
TL/F/5824-43

FIGURE 25. Dual TTL-to-MOS Driver



TL/F/5824-44

FIGURE 26. Dual MOS-to-TTL Driver



Termination is made at the receiving end as follows:
 Line 1 is terminated to ground through Z_0/Z ;
 Line 2 is terminated to +5V through Z_0/Z ,
 where Z_0 is the line impedance.

FIGURE 27. Balanced Line Driver

TL/F/5824-45

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Typical Applications (Continued)

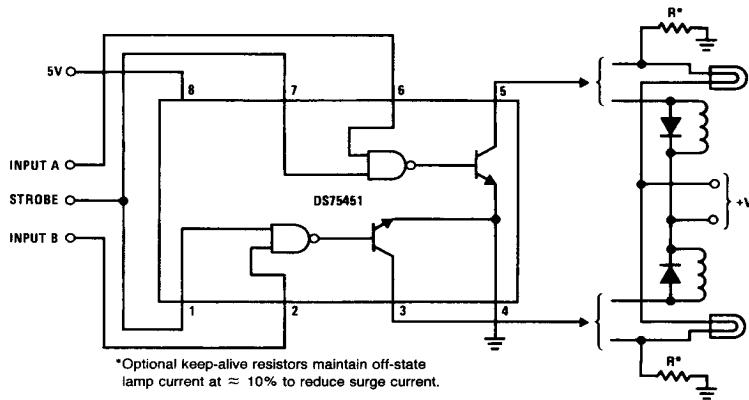


FIGURE 28. Dual Lamp or Relay Driver

TL/F/5824-46

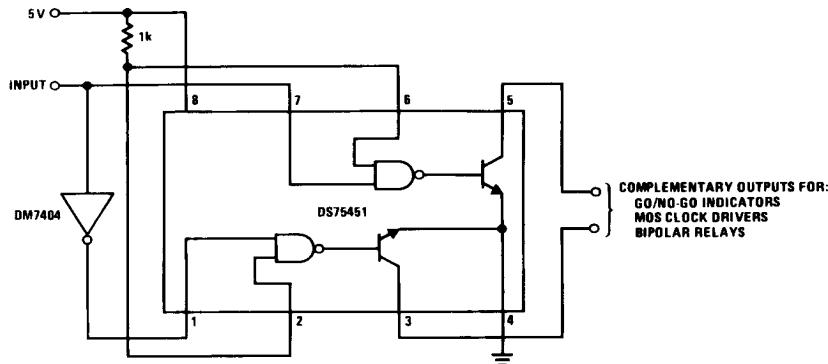
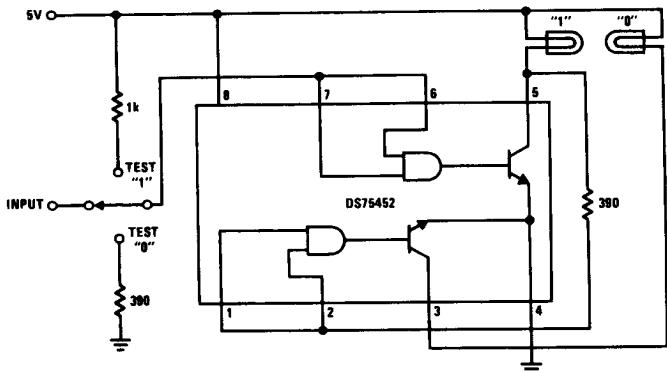


FIGURE 29. Complementary Driver

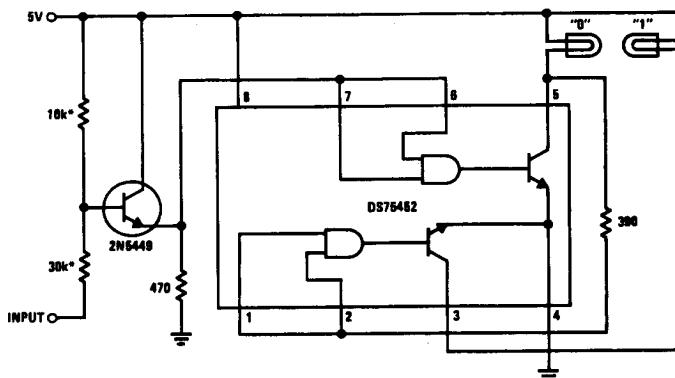
TL/F/5824-47

Typical Applications (Continued)



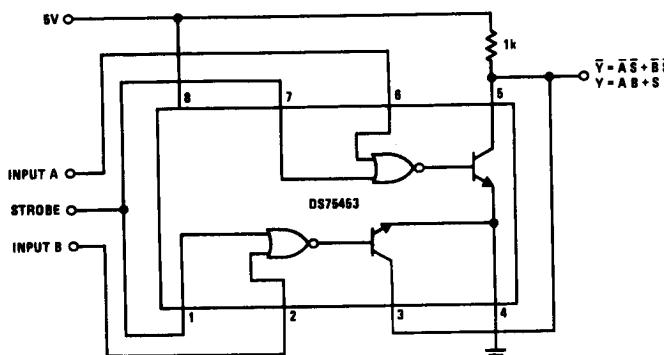
TL/F/5824-48

FIGURE 30. TTL or DTL Positive Logic-Level Detector



TL/F/5824-49

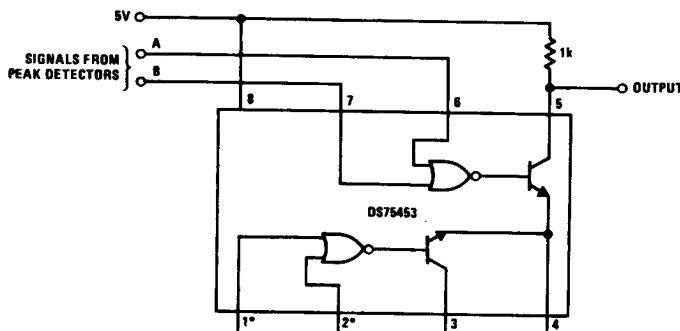
FIGURE 31. MOS Negative Logic-Level Detector



TL/F/5824-50

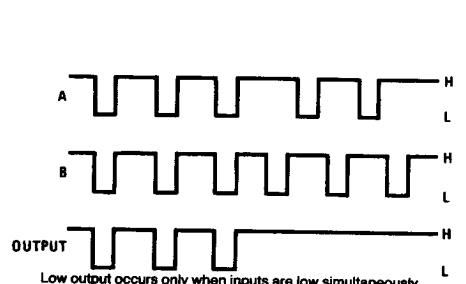
FIGURE 32. Logic Signal Comparator

Typical Applications (Continued)



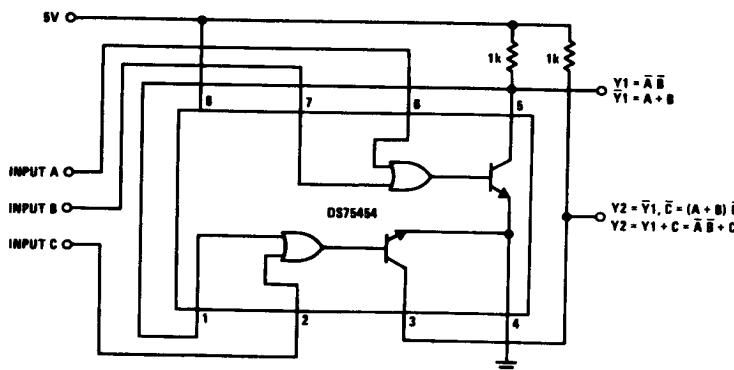
TL/F/5824-51

*If inputs are unused, they should be connected to +5V through a 1k resistor.



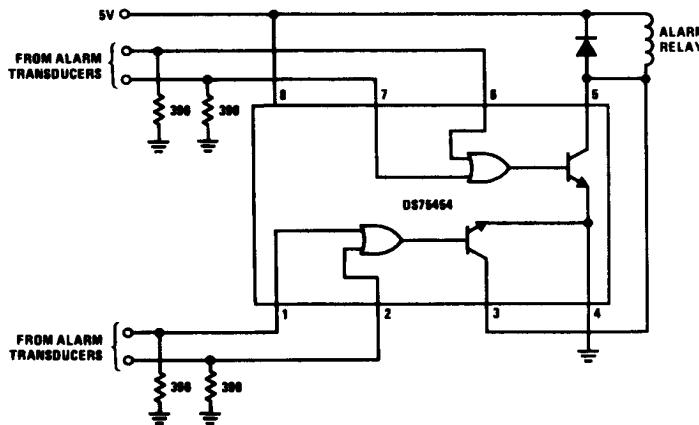
TL/F/5824-52

FIGURE 33. In-Phase Detector



TL/F/5824-53

FIGURE 34. Multifunction Logic-Signal Comparator

Typical Applications (Continued)

TL/F/5824-54

FIGURE 35. Alarm Detector